

BC214

PNP General Purpose Amplifier

- This device is deisgned for use as general purpose amplifiers and switches requiring collector currents to 300mA.
- Sourced from process 68.



1. Collector 2. Base 3. Emitter

Absolute Maximum Ratings* T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{CBO}	Collector-Base Voltage	-45	V
V _{EBO}	Emitter-Base Voltage	-5.0	V
I _C	Collector Current (DC) Continuous	-500	mA
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Electrical Characteristics T_a=25°C unless otherwise noted

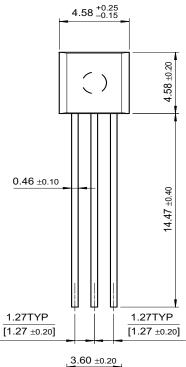
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characte	eristics	•			•
V _{(BR)CEO}	Collector-Emitter Voltage	$I_{C} = -2mA, I_{B} = 0$	-30		V
V _{(BR)CBO}	Collector-Base Voltage	$I_{C} = -10\mu A, I_{E} = 0$	-45		V
V _{(BR)EBO}	Emitter-Base Voltage	$I_E = -10\mu A, I_C = 0$	-5.0		V
I _{CBO}	Collector Cut-off Current	V _{CB} = -30V, I _E = 0		-15	nA
I _{EBO}	Emitter Cut-off Current	V _{EB} = -4V, I _C = 0		-15	nA
On Characte	eristics *	·			
h _{FE}	DC Current Gain	V_{CE} = -5V, I_{C} = -10 μ A V_{CE} = -5V, I_{C} = -2mA V_{CE} = -5V, I_{C} = -100mA	100 140 120	400	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5mA		-0.25 -0.6	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = -100mA, I _B = -5mA		-1.1	V
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = -5V, I_{C} = -2mA$	-0.6	-0.72	V
Small Signa	I Characteristics	•			•
f _T	Current gain Bandwidth Product	V _{CE} = -5V, I _C = -10mA f = 100MHz	200		MHz
NF	Noise Figure	V_{CE} = -5V, I_{C} = -200μA R_{G} = 2k Ω , f = 15.7KHz		2.0	dB
h _{fe}	Small Signal Current Gain	I_C = -2mA, V_{CE} = -5V f = 1KHz	140	600	
C _{OB}	Output Capacitance	V _{CB} = -10V, f = 1MHz		10	pF

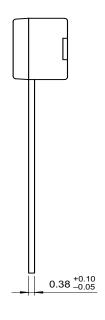
* Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%

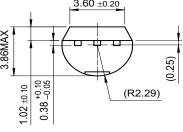
Thermal Characteristics T _A =25°C unless otherwise noted					
Symbol	Parameter	Max.	Units		
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C		
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W		
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W		

Package Dimensions

TO-92







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